2016 International Symposium on Semiconductor Manufacturing (ISSM 2016)

Tokyo, Japan 12-13 December 2016



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Symposium Schedule (Day-1)

ISSM2016 Monday, December 12th, 2016

8:30-	Registration
Room: KFC	C Hall
9:00-9:10	Opening Remarks
	Shozo Saito, Chairman of Organizing Committee of ISSM2016 / Toshiba
9:10-9:15	ISSM 2016
	Shuichi Inoue, Chairman of Executive Committee of ISSM2016 / Renesas Semiconductor Manufacturing
9:15-9:20	ISSM 2016 Program Outline
	Toshiyuki Uchino, Chairman of Program Committee of ISSM2016 / Hitachi Kokusai Electric
9:20-10:00	Keynote Speech: "Minimal Fab using half-inch wafers to reduce a fab investment to 1/1,000"
	Dr. Shiro Hara, Group Leader, Minimal System Group, Nanoelectronics Research Institute,
	National Institute of Advanced Industrial Science and Technology (AIST)
	Session Chair: Kazunori Kato, Advanced Interface Technology (AiT)
10:00-10:40	Keynote Speech: "Toyota's Efforts Toward Realizing a Sustainable Society"
	Dr. Takahiro Ito, General Manager, Process Development Dept.,
	Power Electronics Development Div. TOYOTA MOTOR CORPORATION
	Session Chair: Shuichi Inoue, Renesas Semiconductor Manufacturing
10:40-10:50	Break
10:50-11:30	Keynote Speech: "An overview of smart factories in Industry 4.0 implementation"
	Dr. Jonathan Chang, Senior Director, Backend, Factory Integration, SCM, Infineon Technologies
	Session Chair: Shuichi Inoue, Renesas Semiconductor Manufacturing
11:30-12:30	Lunch Break

Room1: KFC Hall

	L. KFC Hall Geneles - IsT and Dis Data Calution	
	Highlight Session – IoT and Big Data Solution	
Session Co-Chairs:		
Shin-ichi Imai, Panasonic / C. Hsu, TSMC / SC Chang, National Taiwan University		
40.00	MC-O-24 : Data Mining Approaches to Optimize the Allocation of	
12:30	Production Resources in Semiconductor Wafer Fabrication 1	
	Chih-Min Yu, YouThought	
12:50	PC-O-51 : ASML : a Decade of Big Data use 5	
	Rogier Kuijper, ASML	
	PC-O-62 : Distributed Database and Application Architecture for	
13:10	Big Data Solutions 8	
	Makoto Misaki, Panasonic	
	YE-O-50 : A Comprehensive Big-Data-Based" Monitoring System	
13:30	for Yield Enhancement in Semiconductor Manufacturing" 12	
	Kouta Nakata, Toshiba	
13:50	Author's interview & Break	
	YE-O-13 : Visualization technique of maintenance work with	
14:10	motion capture sensors 15	
	Munehito Kagaya, Tokyo Electron	
14:30	PC-O-71 : Unstructured Data Treatment for Big Data Solutions 19	
14.50	Shintaro Sato, Panasonic	
	PC-O-60 : Automatic Property Visualization for Material Survey	
14:50	Support 23	
	Masayuki Okamoto, Toshiba	
15:10	Author's Interview & Break	
	Manufacturing Control and Execution (MC) & eMDC Invited	
Session C		
Masami A	oki, KLA-Tencor Japan / Masahiro Shimbo, ON Semiconductor	
	<emdc2016 invited=""> : Prioritization of Key In-Line Process</emdc2016>	
15:30	Parameters for Electrical Characteristic Optimization of 16-nm	
	High-k Metal Gate Bulk FinFET Devices N/A	
	Dr. Ping-Hsun Su, National Chiao Tung University <emdc2016 invited=""> MC-O-9 : Heuristic Methods for Q-time</emdc2016>	
15:50	Bottleneck Dispatching N/A	
13.50	Ching-Lung Chang, Winbond Electronics	
	<emdc2016 invited=""> MC-O-19 : Generalized Overall Equipment</emdc2016>	
16:10	Effectiveness for Integrated Scheduling and Process Control 27	
	Yu-Ting Kao, National Taiwan University	
	MC-O-43 : Dynamic Cycle-time Improvement through Big Data	
16:30	Analytics 31	
10.50		
	Chih Ming CHAN, GlobalFoundries	
	MC-O-67 : Simultaneous Assignments of Multiple Types of Production Resources in Semiconductor Manufacturing 35	
16:50		
	Hiroyuki Motomiya, University of Tsukuba	
	MC-O-73 : Optimal Production and Capacity Planning for	
17:10	Make-to-Order type Semiconductor Production Systems 39	
	Huizhen BU, University of Tsukuba	
17:30	Author's Interview	
17.50	Walsome Describer @ Forcer	

Room	2: KFC Hall Annex	
	Process and Material Optimization (PO)	
Session Co-Chairs: Kenji Watanabe, SanDisk / Yuji Yamada, Toshiba		
50551011 00	PO-O-21 : Plasma Erosion Behavior of Yttrium Oxide film formed	
12:30	by ADM 73	
	Hiroaki Ashizawa, TOTO	
	PO-O-22 : Sub-10 nm Metal Wire Circuit Fabrication using Directed	
	Self-Assembly of Block Copolymers N/A	
12:50	Tsukasa Azuma, Evolving Nano Process Infrastructure Development	
	Center (EIDEC)	
	PO-O-30 : EEPROM retention performance modulation by poly Si	
13:10	grain size & dopant distribution 77	
	Guai Guan Hong, GlobalFoundries	
	PO-O-31 : STI HDP process effect on yield of embedded memory	
13:30	processes 81	
	Guai Guan Hong, GlobalFoundries	
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	PO-O-37 : Challenges for immersion lithography extension based	
14:10	on negative tone imaging (NTI) process 84	
14.10	Toru Fujimori, FUJIFILM	
	PO-O-58 : Improvement of Particle Generation in a Dry Etching	
14:30	Apparatus 88	
14.50	Tetsuyuki Matsumoto, Toshiba	
	PO-O-68 : Investigation of plasma-induced damage in silicon	
14:50	trench etching 91	
	Shuichi Kuboi, Toshiba	
15:10	Author's Interview & Break	
Session: P	Process Control and Monitoring (PC) & Environment, Safety and	
Health (ES	S)	
Session Co	p-Chairs: Shinsuke Mizuno, Applied Materials Japan / C. Hsu, TSMC	
	PC-O-8 : Advanced Fault Detection Method for Chemical	
15:30	Mechanical Polisher 95	
	Yohei Hamaguchi, Renesas Semiconductor Manufacturing	
	PC-O-14 : Flash gate optimized process and integration for electrical	
15:50	performances requirement on advanced embedded memory 99	
	Agharben El Amine, EMSE-CMP	
46.40	PC-O-42 : Etching Rate Drifts and Drops Induced by Metal Etching	
16:10	Processes N/A	
	Kosuke Yamamoto, Tokyo Electron	
16:30	PC-O-47 : Developing R2R controller by means of studying the sources of variability in plasma etch process 103	
10:50	Agnès Roussy, EMSE-CMP	
	PC-O-59 : Process Optimizer for adjusting film thickness and in-film	
	dopant concentration at the same time 107	
16:50	•	
	Yuichi Takenaga, Tokyo Electron	
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17:10	opportunities for saving power consumption by production tools 111	
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17:30	Author's Interview	
17.00		

Symposium Schedule (Day-2)

ISSM2016 Tuesday, December 13th, 2016

8:30-	Registration
Room: KFC	Hall
8:55	Introduction of Day 2 program Dr.Avako Shimazaki, Executive Vice Chairman of Program Committee of ISSM2016 / Toshiba Nanoanalysis
9:00-10:40	Tutorial Session:
	Session Co-Chairs: Keiji Horioka, Applied Materials Japan / Dr.Ayako Shimazaki, Toshiba Nanoanalysis
9:00-9:50	"Changing semiconductor production management system"
	Tetsuya Kubo, Group Manager, Analysis & Data Management Promotion Group, It & Business Transformation Division, Toshiba Corporatio
	Storage & Electronic Devices Solutions Company
9:50-10:40	"Semiconductors and their band diagrams"
	Prof. Shinichi Takagi, Professor, School of Engineering, The University of Tokyo
10:40-10:50	Break
10:50-11:30	Keynote Speech: "Toward Sustainable Nanometer Manufacturing Technologies in the 2020s"
	Dr. Jack Sun, VP of R&D and CTO, TSMC
	Session Chair : Robert Chien, TSMC
11:30-12:50	Evolution and revitalization of legacy Fabs Session Keynote
	Session Chair: Takeshi Akimoto, Renesas Semiconductor Manufacturing
11:30-12:10	"An overview of optimized automation of 8-inch fab manufacturing lines"
10 10 10 50	Heinz Martin Esser, CEO, Fabmatics GmbH, Board Member of Silicon Saxony e.V
12:10-12:50	"Challenges and Innovations in a 200mm Wafer Fab"
12:50-13:30	Peter Kailbauer, Senior Manager Fab support and strategy, Fab B, ams AG Lunch Break
13:30-14:10	Keynote Speech: "New Era of Electrification and Vehicle Intelligence"
15.50 14.10	Dr. Haruyoshi Kumura, Fellow, Nissan Motor
	Session Chair: Toshiyuki Uchino, Hitachi Kokusai Electric
14:10-14:40	3miniutes Summary presentation by Interactive Poster Speakers
	Session Chair: Toshiharu Katayama, Renesas Semiconductor Manufacturing

Room1: KFC Hall

	Highlight Session : High reliability device process technology for automotive		
and medi	and medical applications		
Session Co	Session Co-Chairs: Isamu Namose, OMRON AUTOMOTIVE ELECTRONICS /		
SC Chang,	National Taiwan University		
	DM-O-11 : Layout-based Test Coverage Verification for High		
14:50	Reliability Devices 43		
	Yoshikazu Nagamura, Renesas Semiconductor Manufacturing		
	PC-O-55 : New Method of Screening Out Outlier(Expanded "PAT"		
15:10	during Package Test) 47		
	Tadashi Sakamoto, Japan Semiconductor		
	<emdc2016 invited=""> DM-O-63 : Fundamentals of side isolation</emdc2016>		
15:30	LDMOS device with 0.35um CMOS compatible process N/A		
	R.Deivasigamani, Asia University		
	DM-O-65 : Study on High-Side LDMOS Energy Capability		
15:50	Improvement 50		
	Yun-Jung Lin, Asia University		
	PO-O-72 : High-Temperature-Resistant Interconnection by Using		
16:10	Nickel Nano-particles for Power Devices Packaging. 54		
	Tomonori lizuka, Waseda University		
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Session :	Process & Metrology Equipment (PE) & Contamination Control and		
Session : Ultraclear	Process & Metrology Equipment (PE) & Contamination Control and n Technology (UC) & Yield Enhancement Methodology (YE)		
Session : Ultraclear Session Co	Process & Metrology Equipment (PE) & Contamination Control and n Technology (UC) & Yield Enhancement Methodology (YE) p-Chairs:		
Session : Ultraclear Session Co	Process & Metrology Equipment (PE) & Contamination Control and n Technology (UC) & Yield Enhancement Methodology (YE) Chairs: Nemoto, Hitachi High-Technologies / Misako Saito, Tokyo Electron		
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Session : Ultracleau Session CC Kazunori 16:50 17:10 17:30	Process & Metrology Equipment (PE) & Contamination Control and n Technology (UC) & Yield Enhancement Methodology (YE) o-Chairs: Nemoto, Hitachi High-Technologies / Misako Saito, Tokyo Electron PE-0-10: Contactless device for the fast conductivity characterization of a large range semiconductors 57 F.LOETE, Centralesupelec UC-0-7: Extended Contamination Control in Advanced Wafer Processing 61 Markus Pfeffer, Fraunhofer IISB UC-0-18: Investigation into behavior of mobile ions in storage device using ToF-SIMS 66 Nobuhito Kuge, Toshiba YE-0-56: STI Si Damage Defect Reduction by HDP Profile Optimizations 70		
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	2: KFC Hall Annex
Highlight Session : Evolution and revitalization of legacy Fabs	
Session C	
	kimoto, Renesas Semiconductor Manufacturing /
Hiroyuki I	noue, Texas Instruments Japan
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15:10	PO-O-4 : A Theoretical Modeling of CMP: A Monte-Carlo Approach 120
15.10	Akira Endou, FUJIMI INCORPORATED
15:30	PE-O-34 : Metrologies of Behavior of Abrasives for Understanding and UPgrading CMP Process 124 Shohei Shima, EBARA
15:50	PO-O-5 : Development of novel CMP slurry for FEOL processes 128
	Yasuyuki Yamato, FUJIMI INCORPORATED
16:10	UC-O-6 : Particle removal efficiency evaluation of filters in IPA 132
10.10	Tomoyuki Takakura, Nihon Pall
16:30	Author's Interview & Break
	Session : Evolution and revitalization of legacy Fabs
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Takahiro	Tsuchiya, Mie Fujitsu Semiconductor
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16:50	Kazuya Dobashi, Tokyo Electron
	YE-O-26 : Improving Process Tool Productivity by Correct Sealing
17:10	Material Selection for Plasma Processes 140
17.10	Murat Gulcur, IDEX Sealing Solutions - PPE
	UC-O-49 : Particle Adsorption onto Si Wafers in Ultrapure Water;
17:30	its Mechanism and Effect of Carbon Dioxide 144
	Koji Nakata, Kurita Water Industries
47.50	MC-O-41 : Revitalizing the 200mm Fabs through Automation 148
17:50	MC-O-41 : Revitalizing the 200mm Fabs through Automation 148 Chih Ming CHAN, GlobalFoundries

ISSM2016

Tuesday, December 13th, 2016

Interactive Poster Session

14:10-14:40 3-min Summary Presentation for Interactive Poster Session @ Room 1 : KFC Hall

Room1	Room1 : KFC Hall		
Session Cha	Session Chair: Toshiharu Katayama, Renesas Semiconductor Manufacturing		
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	Toshiya Ozaki, Toshiba		
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1012-6-11	Supika Mashiro, Tokyo Electron		
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PC-P-38	Monitoring method for deposited film causing particles in mass-production plasma etching process using a load impedance monitoring system 161		
	Yuji Kasashima, National Institute of Advanced Industrial Science and Technology(AIST)		
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PO-P-15	Konrad Schwanitz, WIKA Alexander Wiegand SE & Co. KG		
PO-P-17	Study for Phosphorus Contamination to High Voltage Transistors 169		
	LIANG, LI, GlobalFoundries		
PO-P-61	Research and development of metal-based resist materials for EUVL N/A		
	Julius Joseph Santillan, Evolving nano process Infrastructure Development Center (EIDEC)		
PO-P-64	The Effect of Slurry pH and Particle Size on LiTaO3 Polishing 173		
r0-r-64	Kazuki Moriyama, Nittahaas		
	Electrical characterisation of Metal contacts to 4H-SiC Enhanced by Pre-Metallisation Surface Treatment 176		
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